DATA SHEET

NEC

MOS FIELD EFFECT TRANSISTOR
2SK3755

SWITCHING
N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3755 is N-channel MOS Field Effect Transistor designed for high current switching applications.

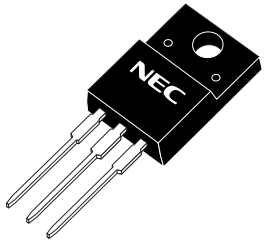
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3755	Isolated TO-220

FEATURES

- Super low on-state resistance
  $R_{DS(on)1}$ = 12 mΩ MAX. (V_{GS} = 10 V, I_D = 23 A)
  $R_{DS(on)2}$ = 18 mΩ MAX. (V_{GS} = 4.5 V, I_D = 23 A)
- Low C_{iss}: C_{iss} = 1200 pF TYP.
- Built-in gate protection diode

(Isolated TO-220)



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	40	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	±20	V
Drain Current (DC) (T_C = 25°C)	$I_{D(DC)}$	±45	A
Drain Current (pulse) Note1	$I_{D(pulse)}$	±140	A
Total Power Dissipation (T_C = 25°C)	P_{T1}	24	W
Total Power Dissipation (T_A = 25°C)	P_{T2}	2.0	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C
Single Avalanche Current Note2	I_{AS}	23	A
Single Avalanche Energy Note2	E_{AS}	53	mJ
Repetitive Avalanche Energy Note3	E_{AR}	53	mJ

Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Starting T_{ch} = 25°C, V_{DD} = 20 V, R_G = 25 Ω, V_{GS} = 20 → 0 V

3. I_{AR} ≤ 23 A, T_{ch} ≤ 150°C

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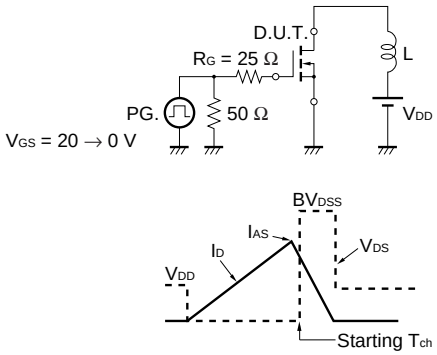
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

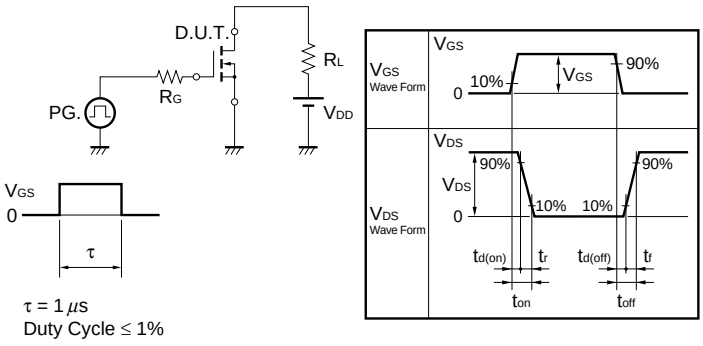
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V			10	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±10	μA
Gate Cut-off Voltage	$V_{GS(off)}$	V_{DS} = 10 V, I_D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance Note	$\|y_{fs}\|$	V_{DS} = 10 V, I_D = 23 A	12	25		S
Drain to Source On-state Resistance Note	$R_{DS(on)1}$	V_{GS} = 10 V, I_D = 23 A		9.7	12	mΩ
	$R_{DS(on)2}$	V_{GS} = 4.5 V, I_D = 23 A		12.9	18	mΩ
Input Capacitance	C_{iss}	V_{DS} = 10 V		1200		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V		330		pF
Reverse Transfer Capacitance	C_{rss}	f = 1 MHz		120		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 20 V, I_D = 23 A		10		ns
Rise Time	t_r	V_{GS} = 10 V		4		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 0 Ω		35		ns
Fall Time	t_f			5		ns
Total Gate Charge	Q_G	V_{DD} = 32 V		25.5		nC
Gate to Source Charge	Q_{GS}	V_{GS} = 10 V		4.2		nC
Gate to Drain Charge	Q_{GD}	I_D = 45 A		7.1		nC
Body Diode Forward Voltage Note	$V_{F(S-D)}$	I_F = 45 A, V_{GS} = 0 V		0.98	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 45 A, V_{GS} = 0 V		29		ns
Reverse Recovery Charge	Q_{rr}	di/dt = 100 A/μs		30		nC

Note Pulsed

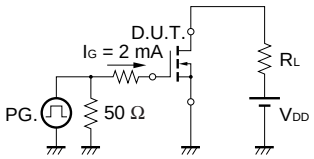
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

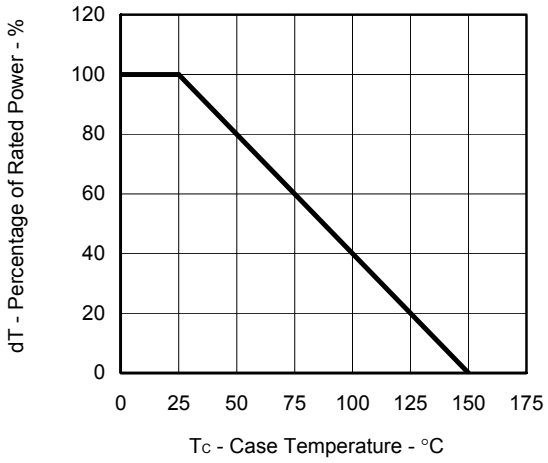


TEST CIRCUIT 3 GATE CHARGE

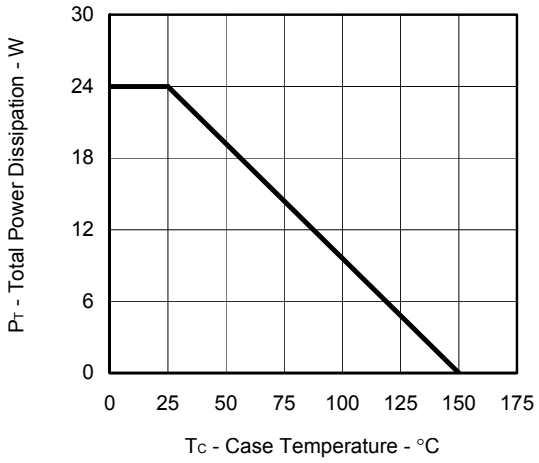


TYPICAL CHARACTERISTICS (T_A = 25°C)

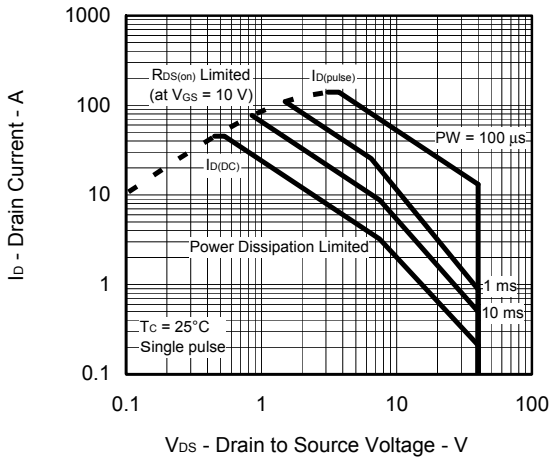
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



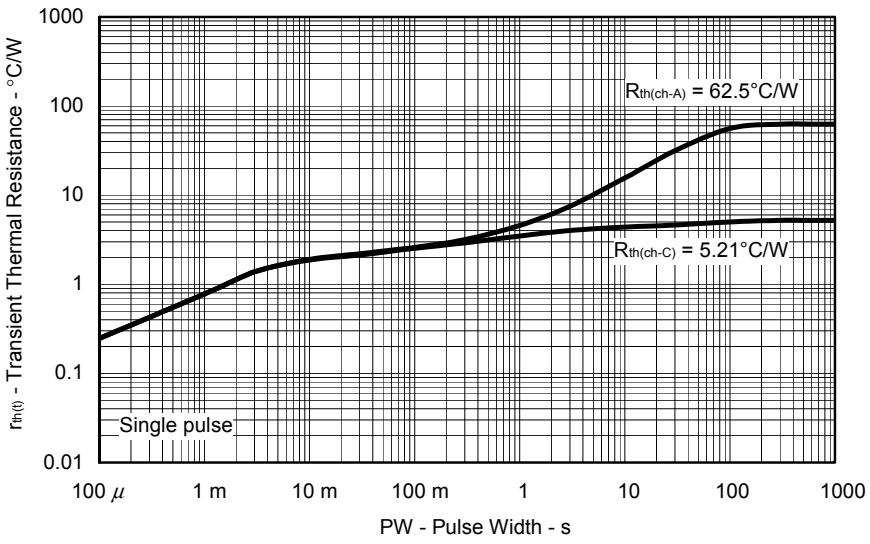
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



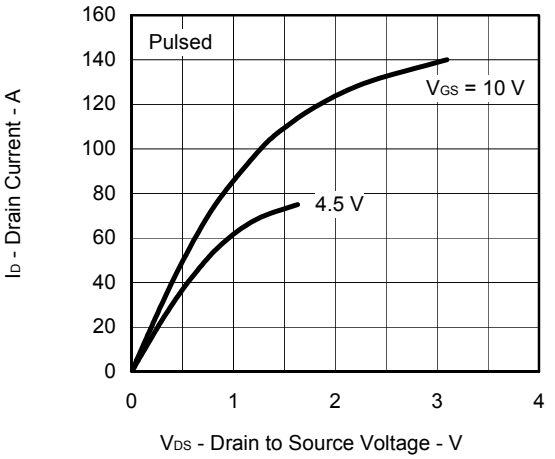
FORWARD BIAS SAFE OPERATING AREA



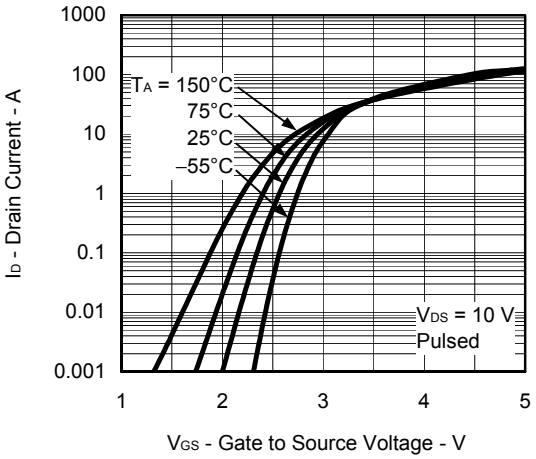
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



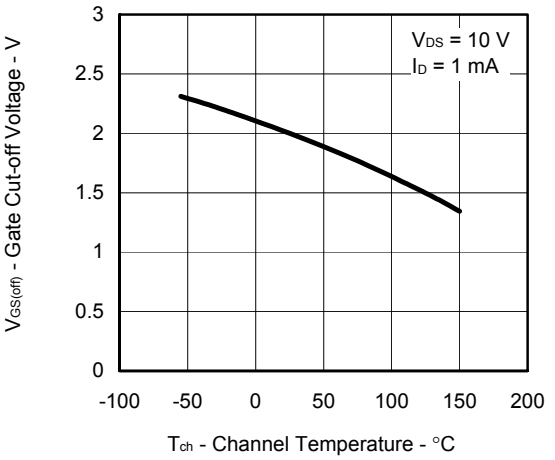
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



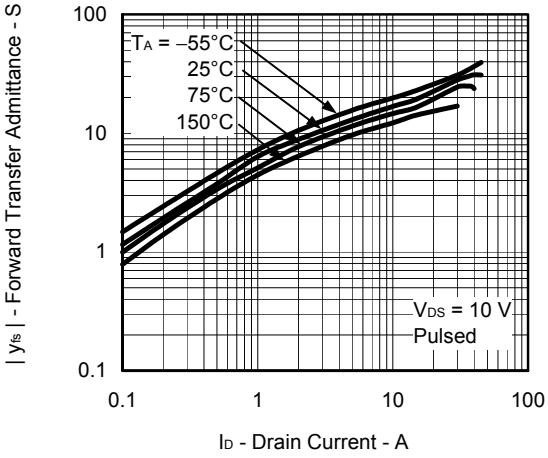
FORWARD TRANSFER CHARACTERISTICS



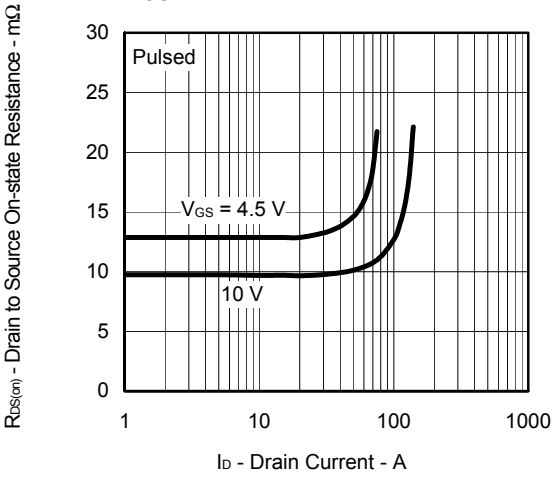
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



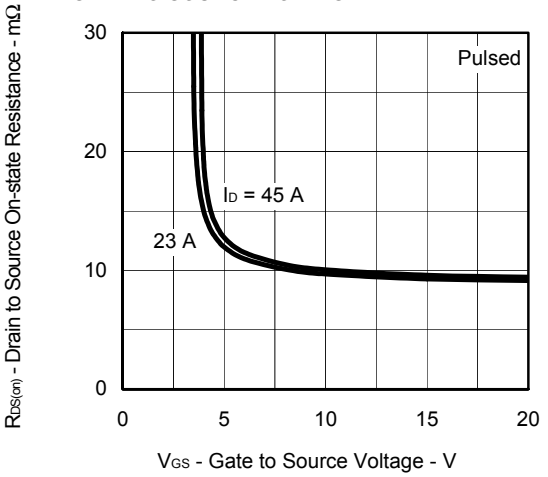
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



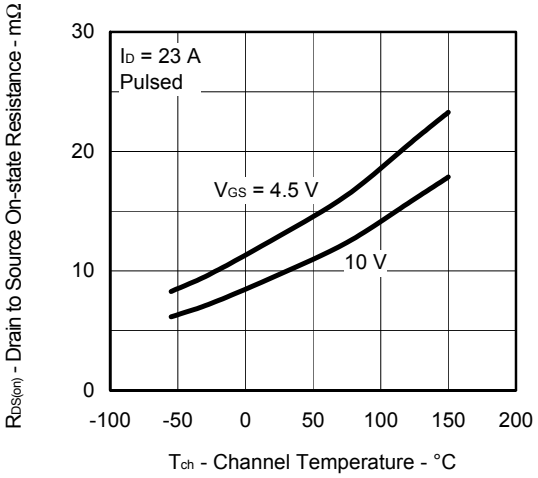
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



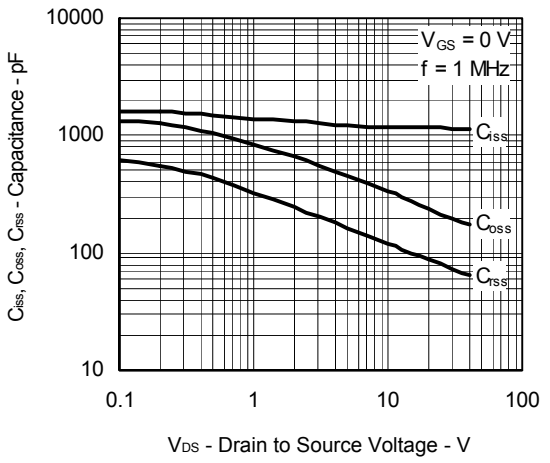
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



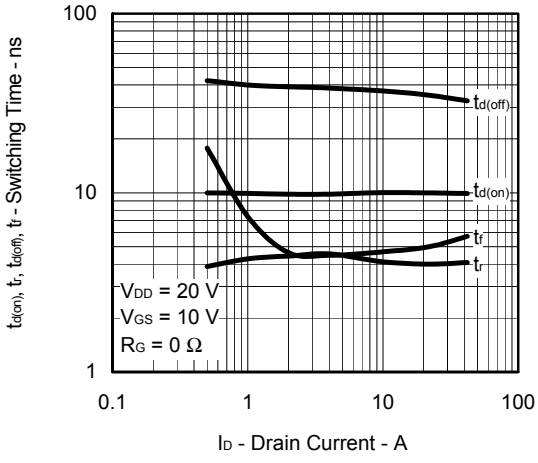
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



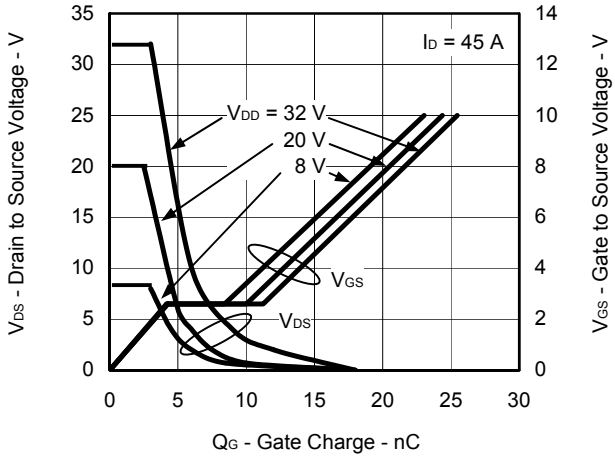
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



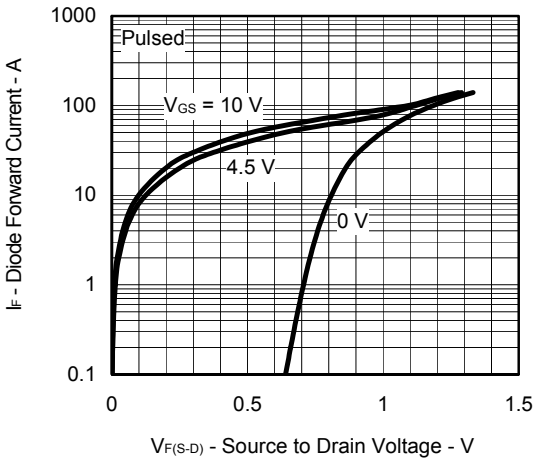
SWITCHING CHARACTERISTICS



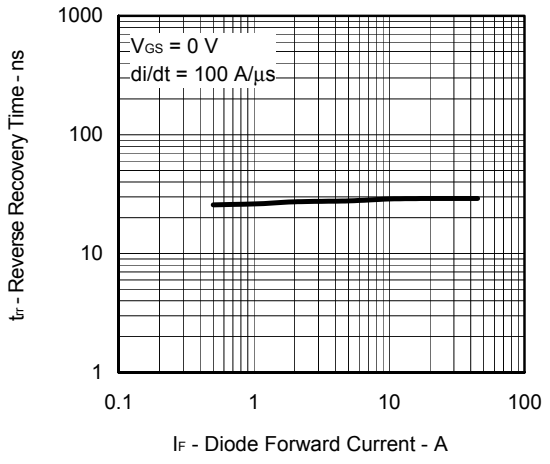
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



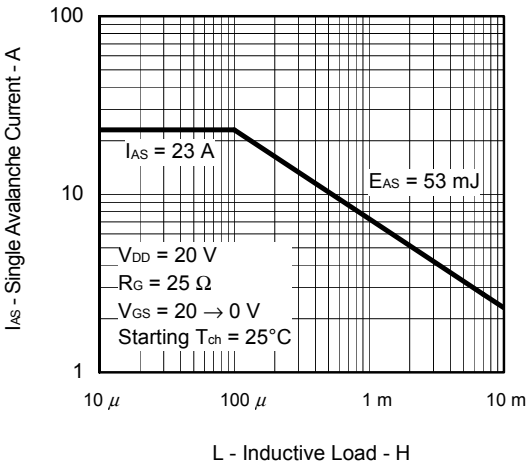
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



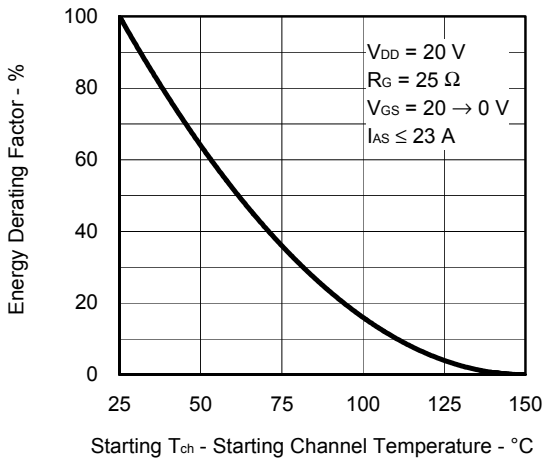
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs.
INDUCTIVE LOAD

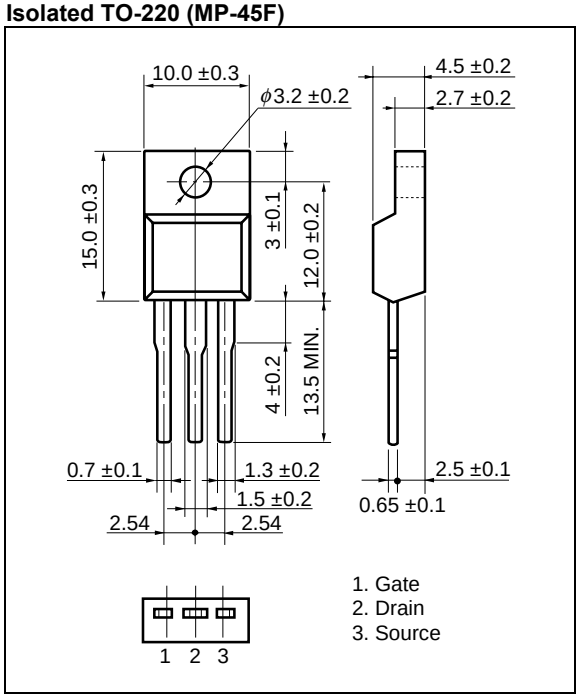


SINGLE AVALANCHE ENERGY
DERATING FACTOR

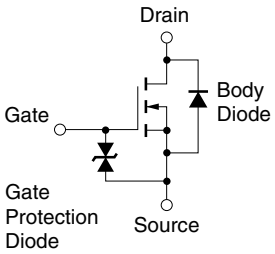


PACKAGE DRAWING (Unit: mm)

Isolated TO-220 (MP-45F)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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